Power MOSFET 20V, $104m\Omega$, 2A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 1.2V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

• Load Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±9	٧
Drain Current (DC)	ID	2	Α
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	IDP	8	Α
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

THERMAE REGIOTARGE TATINGS					
Parameter	Symbol	Value	Unit		
Junction to Ambient When mounted on ceramic substrate (900mm²×0.8mm)	$R_{ heta JA}$	156.2	°C/W		

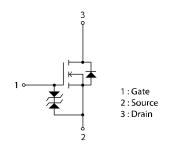


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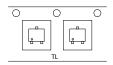
VDSS	R _{DS} (on) Max	ID Max
20V -	104mΩ@ 4.5V	
	147mΩ@ 2.5V	2A
	203mΩ@ 1.8V	ZA
	540mΩ@ 1.2V	

ELECTRICAL CONNECTION N-Channel



PACKING TYPE : TL

MARKING





ORDERING INFORMATION

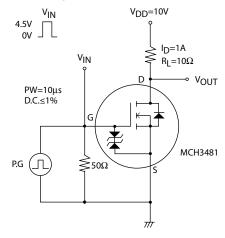
See detailed ordering and shipping information on page 5 of this data sheet.

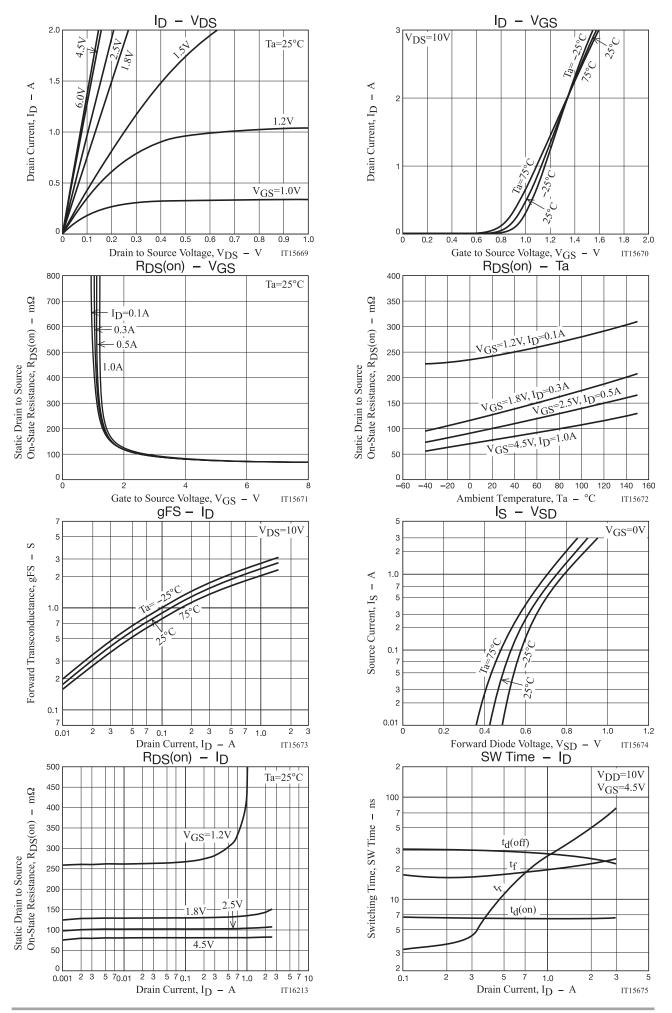
ELECTRICAL CHARACTERISTICS at $Ta = 25^{\circ}C$ (Note 2)

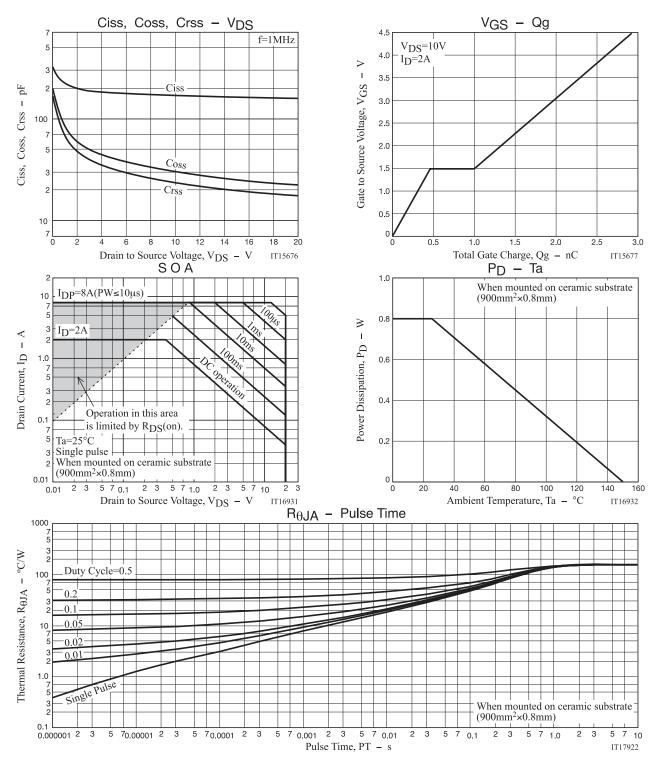
Parameter	Cumbal	Conditions		Value			
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V				V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate to Source Leakage Current	IGSS	V _{GS} =±7.2V, V _{DS} =0V			±10	μΑ	
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	0.3		0.9	٧	
Forward Transconductance	gFS	V _{DS} =10V, I _D =1A		2.4		S	
	R _{DS} (on)1	I _D =1A, V _{GS} =4.5V		80	104	mΩ	
Static Drain to Source On-State	R _{DS} (on)2	I _D =0.5A, V _{GS} =2.5V		105	147	mΩ	
Resistance	R _{DS} (on)3	I _D =0.3A, V _{GS} =1.8V		135	203	mΩ	
	R _{DS} (on)4	I _D =0.1A, V _{GS} =1.2V		270	540	mΩ	
Input Capacitance	Ciss			175		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		30		pF	
Reverse Transfer Capacitance	Crss			25		pF	
Turn-ON Delay Time	t _d (on)			6.6		ns	
Rise Time	t _r	Considered Took Cinquit		27		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		28		ns	
Fall Time	tf			19		ns	
Total Gate Charge	Qg			2.9		nC	
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.46		nC	
Gate to Drain "Miller" Charge	Qgd			0.53		nC	
Forward Diode Voltage	V _{SD}	IS=2A, VGS=0V		0.85	1.2	V	

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit

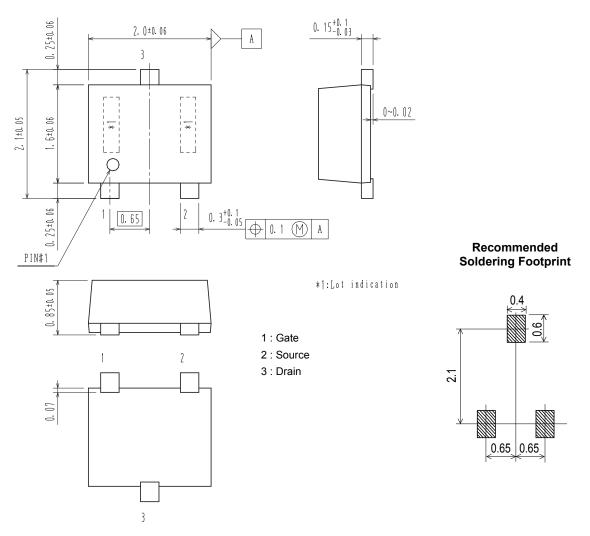






PACKAGE DIMENSIONS

unit:mm SC-70FL/MCPH3 CASE 419AQ ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
MCH3481-TL-H	FNI.	SC-70FL / MCPH3	3,000 / Tape & Reel	
MCH3481-TL-W	FN	(Pb-Free / Halogen Free)		

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH3481 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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